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PARUL UNIVERSITY FACULTY OF ENGINEERING & TECHNOLOGY

B.Tech Mid Semester Exam

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Subject Code: 303192102

Subject Name: Engineering Physics

Date: 21/11/2023 Time: 1hr: 30min Total Marks: 40

		Marks
ir.		05
Q.1	(A) Multiple Choice Question	
1.	is the process by which an incoming photon of a specific frequency can interact with an excited atomic electron, causing it to drop to a lower energy level	
	a) Stimulated radiation b) Stimulated absorption d) Spontaneous absorption	
2.	What role do crystal lattices play in the formation of energy bands?	
	a) Crystal lattices disrupt band formation	
3.	c) Crystal lattices are irrelevant to band formation d) Crystal lattices only affect metallic properties The value of fractional change in the refractive index (Δ) is always optical fibers. a) Positive b) Negative d) None of the above	
4.	Gas lasers havescheme a) Two level pumping b) Three level pumping b) Three level pumping b) Three above	
5.	c) Four level pathprop is/are the characteristics of LASER.	05
1.	What are the types of LASERS, specifically any one of lasers? At higher temperature in intrinsic semiconductors, the position of fermi level gets slightly	
2.	At higher temperature in intrinsic semiconductors, the propagation of light from the optical increased. True or False Mention two necessary conditions for the successful propagation of light from the optical	
3.	Mention two necessary conditions for the successful propagation fiber.	
4. 5.	- a dinala mode oblical mode.	

Q.2	Attempt any four	1
	(1) Explain the construction of the optical fiber in detail	
	(2) Differentiate between Direct band gap and indirect band gap	
	(NA)	
	and the KL W Core and the accentance angle (Q)	
	(*) Derive an expression for the Effective mass (m*)	
Q.3	(a) explain the basic components of lasers	
-	Attempt any two questions	08
	(1) Explain the classification of solid materials based on energy band gap.	
	(2) For an intrinsic semiconductor with a band gap of 0.7 eV, determine the position of E_F at $T = 300$ K if $m_h^* = 6m_h^*$.	
	(3) Calculate the Carrier concentration at 0K and deduce the equation of the fermi energy (E _F).	
Q.4	(A) Explain stimulated absorption, spontaneous emission and stimulated emission in detail	05
	(B) Discuss in detail the construction, theory and working of Ruby laser.	05
	OR	05
	(B) Derive an expression for the carrier concentration of the electrons in intrinsic semiconductor.	05